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SEMICONDUCTOR DEVICES AND METHODS OF MANUFACTURING SEMICONDUCTOR DEVICES

Abstract

In one example, a semiconductor device comprises a cavity substrate comprising a base and a sidewall to define a cavity, an electronic component on a top side of the base in the cavity, a lid over the cavity and over the sidewall, and a valve to provide access to the cavity, wherein the valve has a plug to provide a seal between a cavity environment and an exterior environment outside the cavity. Other examples and related methods are also disclosed herein.

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Background/Summary

CROSS-REFERENCE TO RELATED APPLICATIONS [0001] The present application is a continuation of U.S. application Ser. No. 17/843,789 filed Jun. 17, 2022 (pending), which is a continuation of U.S. application Ser. No. 16/720,603 filed Dec. 19, 2019, now U.S. Pat. No. 11,367,664. Said application Ser. No. 17/843,789, said application Ser. No. 16/720,603, and said U.S. Pat. No. 11,367,664 are hereby incorporated herein by reference in their entireties.

TECHNICAL FIELD

[0002] The present disclosure relates, in general, to electronic devices, and more particularly, to semiconductor devices and methods for manufacturing semiconductor devices.

BACKGROUND

[0003] Prior semiconductor packages and methods for forming semiconductor packages are inadequate, for example resulting in excess cost, decreased reliability, relatively low performance, or package sizes that are too large. Further limitations and disadvantages of conventional and traditional approaches will become apparent to one of skill in the art, through comparison of such approaches with the present disclosure and reference to the drawings.

Description

BRIEF DESCRIPTION OF THE DRAWINGS

[0004] FIG. 1 shows a cross-sectional view of an example semiconductor device.

[0005] FIGS. 2A to 2H show cross-sectional views of an example method for manufacturing an example semiconductor device.

[0006] FIG. 3 shows cross-sectional views of an example method for manufacturing an example semiconductor device.

[0007] FIG. 4 shows a cross-sectional view of an example semiconductor device.

[0008] FIGS. 5A to 5I show cross-sectional views of an example method for manufacturing an example semiconductor device.

[0009] FIG. 6 shows a cross-sectional view of an example semiconductor device.

[0010] FIGS. 7A to 7I show cross-sectional views of an example method for manufacturing an example semiconductor device.

[0011] FIG. 8 shows a cross-sectional view of an example semiconductor device.

[0012] FIGS. 9A to 9H show cross-sectional views of an example method for manufacturing an example semiconductor device.

[0013] FIG. 10 shows a cross-sectional view of an example semiconductor device.

[0014] FIGS. 11A to 11F show cross-sectional views of an example method for manufacturing an example semiconductor device.

[0015] The following discussion provides various examples of semiconductor devices and methods of manufacturing semiconductor devices. Such examples are non-limiting, and the scope of the appended claims should not be limited to the particular examples disclosed. In the following

discussion, the terms “example” and “e.g.” are non-limiting.

[0016] The figures illustrate the general manner of construction, and descriptions and details of well-known features and techniques may be omitted to avoid unnecessarily obscuring the present disclosure. In addition, elements in the drawing figures are not necessarily drawn to scale. For example, the dimensions of some of the elements in the figures may be exaggerated relative to other elements to help improve understanding of the examples discussed in the present disclosure. The same reference numerals in different figures denote the same elements.

[0017] The term “or” means any one or more of the items in the list joined by “or”. As an example, “x or y” means any element of the three-element set {(x), (y), (x, y)}. As another example, “x, y, or z” means any element of the seven-element set {(x), (y), (z), (x, y), (x, z), (y, z), (x, y, z)}. The terms “comprises,” “comprising,” “includes,” or “including,” are “open ended” terms and specify the presence of stated features, but do not preclude the presence or addition of one or more other features. The terms “first,” “second,” etc. may be used herein to describe various elements, and these elements should not be limited by these terms. These terms are only used to distinguish one element from another. Thus, for example, a first element discussed in this disclosure could be termed a second element without departing from the teachings of the present disclosure. Unless specified otherwise, the term “coupled” may be used to describe two elements directly contacting each other or describe two elements indirectly connected by one or more other elements. For example, if element A is coupled to element B, then element A can be directly contacting element B or indirectly connected to element B by an intervening element C. Similarly, the terms “over” or “on” may be used to describe two elements directly contacting each other or describe two elements indirectly connected by one or more other elements.

DESCRIPTION

[0018] In one example, a semiconductor device comprises a cavity substrate comprising a base and a sidewall to define a cavity, an electronic component on a top side of the base in the cavity, a lid over the cavity and over the sidewall, and a valve to provide access to the cavity, wherein the valve has a plug to provide a seal between a cavity environment and an exterior environment outside the cavity.

[0019] In another example, a method to manufacture a semiconductor device comprises providing a cavity substrate comprising a base and a sidewall to define a cavity, providing an electronic component on a top side of the base in the cavity, providing a lid over the cavity contacting the sidewall, and providing a valve to provide access to the cavity, wherein the valve has a plug to provide a seal between a cavity environment and an environment outside the cavity.

[0020] In a further example, a semiconductor device comprises a substrate comprising a base and a sidewall extending vertically from the base, a lid over the sidewall to define a cavity between the base, the sidewall, and the lid, an electronic component in the cavity, a valve between the cavity and an exterior environment outside the cavity, a seal between the lid and the sidewall, and a plug in the valve, wherein the seal and the plug hermetically seal the cavity from the exterior environment.

[0021] Other examples are included in the present disclosure. Such examples may be found in the figures, in the claims, or in the description of the present disclosure.

[0022] FIG. 1 shows a cross-sectional view of an example semiconductor device **10**. In the example shown in FIG. 1, semiconductor device **10** can comprise cavity substrate **11**, electronic component **15**, interconnect **14**, lid **13**, seal **16**, valve **18**, and plug **19**.

[0023] Cavity substrate **11** can comprise conductive structure **111** and dielectric structure **112**. Conductive structure **111** can comprise substrate internal terminal **1111**, substrate external terminal **1112**, conductive path **1113** and seal base **1114** (optional). Conductive structure **111** can be in base **112A** and can be electrically coupled with electronic component **15**. Dielectric structure **112** can comprise base **112A** and sidewall **112B**. Cavity **113** can be defined by base **112A** and sidewall **112B**. Cavity environment or volume **1131** can be implemented in cavity **113**. Electronic

component **15** can comprise component terminal **151**. Valve **18** can comprise tap **181**. In some examples, cavity substrate **11** can comprise base **112A** and sidewall **112B** to define cavity **113**. [0024] In some examples, lid **13** can be over cavity **113** and sidewall **112B** of cavity substrate **11**. Cavity substrate **11**, lid **13**, seal **16**, valve **18**, and plug **19** can be referred to as a hermetic semiconductor package and can provide protection for electronic component **15** from external elements or environmental exposure. Valve **18** can provide access to cavity **113** and plug **19** can provide a seal in valve **18** between the cavity environment and an exterior environment outside cavity **113**. Semiconductor package can provide electrical coupling between external electrical components and substrate external terminal **1112**. In some examples, electronic component **15** can be on a top side of base **112A**. Electronic component **15** can include electronic elements or optical elements as an example, and the scope of the disclosed subject matter is not limited in this respect. [0025] FIGS. 2A to 2H show cross-sectional views of an example method for manufacturing semiconductor device **10**. FIG. 2A shows a cross-sectional view of semiconductor device **10** at an early stage of manufacture.

[0026] In the example shown in FIG. 2A, cavity substrate **11** can be provided wherein cavity substrate can comprise base **112A** and sidewall **1114**. Cavity substrate **11** can have a thickness in the range from about 100 micrometers (μm) to about 1500 μm . As described above, cavity substrate **11** can comprise conductive structure **111** and dielectric structure **112**.

[0027] Conductive structure **111** can comprise several elements such as substrate internal terminal **1111**, substrate external terminal **1112**, conductive path **1113**, or seal base **1114**. Substrate internal terminal **1111** can be located at a top of base **112a** of dielectric structure **112** and within cavity **113** of dielectric structure **112**. Substrate external terminal **1112** can be located at a bottom of base **112A** of dielectric structure **112**. Conductive path **1113** can traverse through dielectric structure **112** to couple substrate internal terminal **1111** with substrate external terminal **1112**. In some examples, seal base **1114** can be provided along the periphery of dielectric structure **112** at the top of sidewall **112B**. In some examples, seal base **1114** can be in sidewall **112B** with seal **16** between seal base **1114** and lid **13**. Conductive structure **111** or its elements can comprise or can be referred to as one or more conductive layers, traces, pads, vias, or leads. Substrate internal terminal **1111** can comprise or can be referred to as pads or traces. Substrate external terminal **1112** can also comprise or can be referred to as pads or traces. Conductive path **1113** can comprise or can be referred to as one or more vias or traces. Seal base **1114** can comprise or can be referred to as conductive pads or conductive lands. In some examples, substrate internal terminal **1111**, substrate external terminal **1112**, conductive path **1113**, or seal base **1114** can comprise copper, aluminum, nickel, gold, or silver. In some examples, seal base **1114** can comprise copper, tungsten, or a nickel-gold plating. Elements of conductive structure **111**, such as substrate internal terminal **1111**, substrate external terminal **1112**, conductive path **1113**, or seal base **1114**, can have a thickness in the range from about 10 μm to about 50 μm .

[0028] Dielectric structure **112** can comprise base **112A** and sidewall **112B**. Base **112A** can have a substantially planar top side and a substantially planar bottom side opposite to the top side. Sidewall **112B** can upwardly extend or protrude along the periphery of base **112A**. A vertical thickness of base **112A** can be greater than a horizontal thickness of sidewall **112B**. In some examples, when planarly viewed, sidewall **112B** can be substantially rectangular. Conductive structure **111** can be accessible at the top and bottom sides of base **112A**. In some examples, substrate internal terminal **1111** can be provided on the top side of base **112A**, substrate external terminal **1112** can be provided on the bottom side of base **112A**, and conductive path **1113** can pass through base **112A**. Seal base **1114** can be provided on the top side of sidewall **112B**. As an example, seal base **1114** can be embedded on sidewall **112B** so that the top side of seal base **1114** is substantially coplanar with the top side of sidewall **112B**.

[0029] Dielectric structure **112** can comprise one or more dielectric layers stacked on each other, such as ceramic layers, molded resin layers, or laminate layers. Dielectric structure **112** can have a

thickness in the range from about 100 μm to about 1500 μm . Cavity **113** defined by base **112A** and sidewall **112B** can have a depth in the range from about 100 μm to about 1000 μm .

[0030] In examples where dielectric structure **112** comprises ceramic, dielectric structure **112** can comprise or can be referred to as alumina, silicon nitride, sapphire, or borosilicate glass. In some examples, cavity substrate **11** can be manufactured in a similar manner to that of a low temperature co-fired ceramic (LTCC) substrate. In some examples, the LTCC substrate can generally be co-fired at a low temperature of about 1000° C. or less. The LTCC technology can comprise forming via holes in dielectric sheet having a thickness in the range from about 40 μm to 80 μm and filling the via holes with a conductor or conductive paste to provide conductive path **1113**, printing conductor patterns to provide substrate internal terminal **1111**, substrate external terminal **1112**, or seal base **1114**, coupling valve **18**, laminating, and co-firing. In some examples, an operation for forming seal base **1114** using sputtering and plating can be separately performed. In some examples, an operation for coupling valve **18** to sidewall **112B** of substrate **11** can be performed.

[0031] In some examples, “green sheets” or layers of ceramic and binding agent can be prepared prior to low temperature co-firing. Via holes having an appropriate size can be formed in the green sheets using a punching tool or laser beams, and conductor paste can fill the via holes. The conductor paste filling the via holes can become conductive path **1113**. Then, conductor patterns can be printed. During the conductor pattern printing process, the conductor material can be provided as a desired circuit pattern, for example using printing. As the result of this process, substrate internal terminal **1111**, substrate external terminal **1112**, or seal base **1114** can be provided. Valve **18** can be fixedly inserted into sidewall of one or more green sheets. The respective green sheets can be stacked and adhered to one another by applying heat and pressure. In the co-firing process, binder components can be eliminated or vaporized from the stacks at a temperature ranging from about 300° C. to about 400° C.

[0032] In some examples, cavity substrate **11** can be formed as a molded resin substrate with dielectric structure **112** having one or more layers of molded material. In some examples, cavity substrate **11** can be a pre-formed or laminate substrate having one or more laminate layers as dielectric structure **112**. The pre-formed substrate can be manufactured prior to attachment to an electronic device and can comprise dielectric layers between respective conductive layers. The conductive layers can comprise copper and can be formed using an electroplating process. The dielectric layers can be relatively thicker non-photo-definable layers that can be attached as a pre-formed film rather than as a liquid and can include a resin with fillers such as strands, weaves, or other inorganic particles for rigidity or structural support. Since the dielectric layers are non-photo-definable, features such as vias or openings can be formed by using a drill or lasers. In some examples, the dielectric layers can comprise a prepreg material or Ajinomoto Buildup Film (ABF). The pre-formed substrate can include a permanent core structure or carrier such as, for example, a dielectric material comprising bismaleimide triazine (BT) or FR4, and dielectric and conductive layers can be formed on the permanent core structure. In other examples, the pre-formed substrate can be a coreless substrate which omits the permanent core structure, and the dielectric and conductive layers can be formed on a sacrificial carrier that is removed after formation of the dielectric and conductive layers and before attachment to the electronic device. The pre-formed substrate can be referred to as a printed circuit board (PCB) or a laminate substrate. Such pre-formed substrate can be formed through a semi-additive or modified-semi-additive process.

[0033] Valve **18** can be coupled through sidewall **112B** of dielectric structure **112**. Valve **18** can be coupled through sidewall **112B** of cavity substrate **11** to cavity **113**. In some examples, an inner end of valve **18** can be coplanar with the inner side of sidewall **112B**. In some examples, the inner end of valve **18** can protrude from the inner side of sidewall **112B** into cavity **113**. In some examples, the outer end of valve **18** can outwardly protrude from the outer side of sidewall **112B**. Valve **18** can comprise a passage **182** that can allow air to be discharged from cavity **113**, or can allow gas, such as inert gas or air, to be introduced into cavity **113** to a target pressure. Valve **18** can comprise

or can be referred to as a pipe, a tube, or a passageway. Valve **18** can comprise an orifice or tap **181** leading to passage **182**. Tap **181** can be provided on a region of valve **18** positioned at the exterior side of sidewall **112B**. Valve **18** can comprise kovar, steel, stainless steel, copper, aluminum, or nickel. In some examples, valve **18** can comprise a similar material to that of a lead frame. In some examples, valve **18** can comprise dam **183** formed at a region of passage **182** corresponding to tap **181**. Plug may be positioned in dam **183**. In some examples, dam **183** can comprise a dam perimeter configured to restrain plug **19** from lateral displacement or expansion. A thickness or height of dam **183** can be smaller than a thickness or height of passage **182** of valve **18**. Each of dams **183** can have a thickness in the range from about 10 μm to about 100 μm . Valve **18** can have a diameter in the range from about 50 μm to about 200 μm .

[0034] The completed cavity substrate **11** can comprise cavity **113** and valve **18** providing access to cavity **113** through sidewall **112B** of substrate **11**. In some examples, where dielectric structure **112** of cavity substrate **11** includes ceramic as a major material, high thermal conductivity and chemical stability as well as enhanced high frequency performance and electrical performance can be achieved.

[0035] FIG. 2B shows a cross-sectional view of semiconductor device **10** at a later stage of manufacture. In the example shown in FIG. 2B, electronic component **15** can be provided on cavity substrate **11**. In some examples, electronic component **15** can be provided or attached on top side of base **112A** of cavity substrate **11** using an adhesive or thermal interface material. Electronic component **15** can comprise component terminal **151** at its top side. Electronic component **15** can comprise or can be referred to as a die, a chip, or a package, where the die or the chip can comprise an integrated circuit separated from a semiconductor wafer. The package can be completed by covering the die or the chip using a protective material. Electronic component **15** can comprise, for example, digital signal processors (DSPs), microprocessors, network processors, power management units, audio processors, radio-frequency (RF) circuits, wireless baseband system-on-chip (SoC) processors, sensors, or application specific integrated circuits (ASICs). Electronic component **15** can have a thickness in the range from about 100 μm to about 775 μm . Electronic component **15** can be positioned within cavity **113** of cavity substrate **11** to be protected from external environment or to be provided with a desired operational environment.

[0036] FIG. 2C shows a cross-sectional view of semiconductor device **10** at a later stage of manufacture. In the example shown in FIG. 2C, interconnect **14** can be coupled between electronic component **15** and cavity substrate **11**. One end of interconnect **14** can be electrically connected to component terminal **151** of electronic component **15**, and the other end of interconnect **14** can be electrically connected to substrate internal terminal **1111** of cavity substrate **11**. Interconnect **14** can comprise or can be referred to as a wire or a bump. Interconnect **14** can comprise or can be referred to as gold, copper, aluminum, or solder. In some examples, if component interconnect **151** of electronic component **15** faces upward, interconnect **14** can comprise, for example, a wire and can electrically connect electronic component **15** and cavity substrate **11**. For example, one end of interconnect **14** can be firstly ball-bonded to component terminal **151**, and the other end of interconnect **14** can be secondly stitch-bonded to substrate internal terminal **1111**, or vice versa. In some examples, if component interconnect **151** of electronic component **15** faces downward, interconnect **14** can comprise, for example, a bump and can electrically connect electronic component **15** and cavity substrate **11**. For example, ball-type or pillar-type interconnect **14** can be attached to component terminal **151** or substrate internal terminal **1111** and electronic component **15** can then be attached onto cavity substrate **11** through a mass reflow process, a thermal compression process or a laser assist bonding process. Interconnect **14** can have a diameter in the range from about 15 μm to about 50 μm .

[0037] FIGS. 2D and 2E show a cross-sectional view of semiconductor device **10** at a later stage of manufacture. In the example shown in FIGS. 2D and 2E, lid **13** can be provided on cavity substrate **11**. Lid **13** can have a planar top side and a planar bottom side. The bottom side of lid **13** can be

attached onto sidewall **112B** of cavity substrate **11**. The bottom side of lid **13** can be attached onto seal base **1114** provided on sidewall **112B**. Lid **13** can comprise or can be referred to as a cover or a cap. Lid **13** can comprise or can be referred to as a metal, plastic resin, or ceramic. Lid **13** can have a thickness in the range from about 100 μm to about 500 μm . Lid **13** can be attached to sidewall **112B** of cavity substrate **11** using seal **16**. Seal **16** can be provided on a region of lid **13** corresponding to seal base **1114** located on sidewall **112B**. Seal **16** can comprise or can be referred to as a solder or an adhesive. In some examples seal **16** can be provided on one of lid **13** or seal base **1114** and can then be bonded to another one of lid **13** or seal base **1114** through a mass reflow process, a thermal compression process, or a laser assist bonding process. Seal **16** can have a thickness in the range from about 10 μm to about 100 μm . Lid **13** and seal **16** can cover cavity **113** of cavity substrate **11** to provide protection of electronic component **15** and interconnect **14** from external environment or maintaining a desired environment **1113** within cavity **113**.

[0038] FIG. 2F shows a cross-sectional view of semiconductor device **10** at a later stage of manufacture. In the example shown in FIG. 2F, plug **19** can be provided in valve **18**. Plug **19** can be mounted on tap **181** of valve **18** to occlude tap **181**. Plug **19** can comprise or can be referred to as a microball, a solder, a resin, or an adhesive. In some examples, plug **19** can comprise a lead (Pb) free solder alloy such as a Sn—Ag—Cu alloy, or AuSn solder. A diameter of plug **19** can be slightly larger than that of tap **181**. Plug **19** can have a diameter in the range from about 10 μm to about 150 μm . In this way, tap **181** of valve **18** can be temporarily occluded, passage **182** of valve **18** can be still opened.

[0039] FIG. 2G shows a cross-sectional view of semiconductor device **10** at a later stage of manufacture. In the example shown in FIG. 2G, the air in cavity **113** can be discharged to the exterior side through valve **18** to generate a vacuum in cavity **113**. In the same or other examples, a desired gas such as an inert gas or air can be introduced to a target pressure into cavity **113** through valve **18**. In some examples, the cavity environment can comprise a vacuum or an inert gas. In some examples, vacuum equipment can be connected to valve **18** to release the air in cavity **113** out of cavity, and gas filling equipment can be connected to valve **18** to allow gas to fill cavity **113**. Examples of inert gas can comprise nitrogen, argon, or helium. The internal gas pressure of cavity **113** can be in the range from about 0 millibars (mbar) to about 1100 mbar. Cavity environment **1131** can be provided in which cavity **113** is left as vacuum or is filled with gas.

[0040] FIG. 2H shows a cross-sectional view of semiconductor device **10** at a later stage of manufacture. In the example shown in FIG. 2H, tap **181** and passage **182** of valve **18** can be occluded by plug **19**. In some examples, tap **181** and passage **182** can be occluded by melting plug **19** using, for instance, a laser beam to seal plug **19** in valve **18**. Melted plug **19** can be positioned or can flow between a pair of dams to then be cured, and cured plug **19** can plug passage **182** and tap **181**. Cavity environment **1131** provided in cavity **113** can be isolated from an external environment by cured plug **19**. In some examples, laser beam sources can comprise a carbon dioxide (CO₂) laser, a fiber laser, or an yttrium aluminum garnet (YAG) laser, and lasers can be oscillated in a pulsed laser mode or a continuous wave mode. In some examples, the laser output power can be in the range from about 200 watts (W) to about 20 kilowatts (kW).

[0041] FIG. 3 shows cross-sectional views of an example method for manufacturing an example semiconductor device. In the example shown in FIG. 3, in order to occlude tap **181** and passage **182** of valve **18**, a forced inserting process or a bolting process can be employed instead of a laser beam process. Air in cavity **113** can be removed from cavity **113** through valve **18**, or gas can be introduced into cavity **113** through valve **18** to a target pressure, and then plug **19** or **19A** can be forcedly inserted into or bolted into tap **181** and passage **182**, thereby occluding tap **181** and passage **182** of valve **18**. In this manner, a vacuum can be provided in the cavity environment, or an inert gas can be provided in the cavity environment, and the cavity environment can be maintained by sealing plug **19** or **19A** into valve **18**. In some examples, plug **19** or **19A** can comprise or can be referred to as a soft metal ball, a soft plastic resin ball, or a soft metal ball enclosed with a soft

plastic resin. If plug **19** or **19A**, which is made of a soft material, is forcedly inserted into tap **181**, the shape of plug **19** or **19A** is changed so that tap **181** and passage **182** can be occluded by plug **19** or **19A**. In some examples, the soft material can comprise or can be referred to as a solder, aluminum, gold, or silver, and the soft plastic resin can comprise or can be referred to as polyimide (PI), polypropylene (PP), polyethylene (PE), or a Teflon resin.

[0042] FIG. **4** shows a cross-sectional view of an example semiconductor device **20**.

Semiconductor device **20** shown in FIG. **4** can be similar to example semiconductor device **10** shown in FIG. **1**, and valve **18** is provided between cavity substrate **11** and lid **13**. In the example shown in FIG. **4**, semiconductor device **20** can be configured such that valve **18** is positioned between sidewall **112B** of cavity substrate **11** and lid **13**, rather than being positioned at sidewall **112B** of cavity substrate **11**. Valve **18** can be fixed between sidewall **112B** of cavity substrate **11** and lid **13** by seal **16**.

[0043] FIGS. **5A** to **5I** show cross-sectional views of an example method for manufacturing an example semiconductor device **20**. The manufacturing method of example semiconductor device **20** shown in FIGS. **5A** to **5I** can be similar to corresponding operations or figures described in FIGS. **2A** to **2H**, for example for semiconductor device **10**. FIGS. **5A** to **5I**, however, show valve **18** positioned between cavity substrate **11** and lid **13**. The following description will focus on differences between the methods.

[0044] FIG. **5A** shows a cross-sectional view of semiconductor device **20** at an early stage of manufacture. In the example shown in FIG. **5A**, cavity substrate **11** can be provided without valve **18** attached. Cavity substrate **11** can comprise conductive structure **111** and dielectric structure **112**. Sidewall **112B** of dielectric structure **112** can lack the passageway to which valve **18** was attached in the example of FIGS. **1-2**

[0045] FIG. **5B** shows a cross-sectional view of semiconductor device **20** at a later stage of manufacture. In the example shown in FIG. **5B**, electronic component **15** can be provided on cavity substrate **11**. In some examples, electronic component **15** can be attached onto base **112A** of cavity substrate **11** using an adhesive or a thermally conductive material.

[0046] FIG. **5C** shows a cross-sectional view of semiconductor device **20** at a later stage of manufacture. In the example shown in FIG. **5C**, interconnect **14** can be provided between electronic component **15** and cavity substrate **11**.

[0047] FIG. **5D** shows a cross-sectional view of semiconductor device **20** at a later stage of manufacture. In the example shown in FIG. **5D**, valve **18** can be provided. In some examples, valve **18** can be provided on or attached to cavity substrate **11** on the top of sidewall **112B** or on seal base **1114**. In some examples, valve **18** can be coupled to seal base **1114** by seal **16A**, which can comprise or can be referred to as a solder or an adhesive. In some examples, an inner end of valve **18** can be substantially coplanar with the inner side of sidewall **112B**, or an outer end of valve **18** can protrude past the outer side of sidewall **112B**. Valve **18** can comprise a passage **182** that can allow air to be discharged to the exterior from cavity **113**, or can allow a gas, such as an inert gas, to be injected into cavity **113** from the exterior of cavity **113**. Valve **18** can comprise tap **181** or orifice connected to passage **182**. Tap **181** can be provided on a region of valve **18** positioned at the exterior side of sidewall **112B**.

[0048] FIGS. **5E** and **5F** show a cross-sectional view of semiconductor device **20** at a later stage of manufacture. In the example shown in FIGS. **5E** and **5F**, lid **13** can be provided on cavity substrate **11** and valve **18**. A bottom side of lid **13** can be attached to sidewall **112B** and valve **18** of cavity substrate **11**. The bottom side of lid **13** can be attached onto seal base **1114** provided on sidewall **112B** or onto valve **18**. Lid **13** can be attached to sidewall **112B** of cavity substrate **11** or to valve **18** by seal **16**. Seal **16** can be provided on a region of lid **13** corresponding to seal base **1114** located on sidewall **112B** and a region of lid **13** corresponding to valve **18**, respectively. In some examples, after seal **16** is adhered to lid **13** or to seal base **1114** and valve **18**, lid **13** can be bonded onto seal base **1114**, sidewall **112B**, or valve **18** through a mass reflow process, a thermal compression

process, or a laser assist bonding process. In some examples, seal **16** adhered to lid **13** can be integral with or coupled to seal **16A** adhered between valve **18** and sidewall **112B**. Because valve **18** is positioned between lid **13** and cavity substrate **11**, a thickness of seal **16** can be larger than that of valve **18**.

[0049] FIG. 5G shows a cross-sectional view of semiconductor device **20** at a later stage of manufacture. In the example shown in FIG. 5G, plug **19** can be provided in valve **18**. Plug **19** can be mounted on tap **181** of valve **18** to temporarily occlude tap **181**.

[0050] FIG. 5H shows a cross-sectional view of semiconductor device **20** at a later stage of manufacture. In the example shown in FIG. 5H, air in cavity **113** can be discharged to the exterior side through valve **18**, or a gas such as inert gas or air can be introduced to cavity **113** through valve **18**.

[0051] FIG. 5I shows a cross-sectional view of semiconductor device **20** at a later stage of manufacture. In the example shown in FIG. 5I, tap **181** and passage **182** of valve **18** can be occluded by plug **19**. In some examples, tap **181** and passage **182** can be occluded by melting plug **19** using, for instance, a laser beam, or by performing a forced inserting or bolting process.

[0052] FIG. 6 shows a cross-sectional view of an example semiconductor device **30**. Example semiconductor device **30** shown in FIG. 6 can be similar to example semiconductor device **10** shown in FIG. 1, and valve **38** can be incorporated in cavity substrate **11**. In the example shown in FIG. 6, semiconductor device **30** can be configured such that valve **38** comprises an aperture provided at or in base **112A** of cavity substrate **11**, rather than being positioned at sidewall **112B** of cavity substrate **11**. Base **112A** of cavity substrate **11** can comprise valve **38** and valve base **31**. Semiconductor device **30** can comprise plug **19** positioned in valve **38**.

[0053] FIGS. 7A to 7I show cross-sectional views of an example method for manufacturing an example semiconductor device **30**. The manufacturing method of example semiconductor device **30** shown in FIGS. 7A to 7I can be similar to corresponding operations or figures described in FIGS. 2A to 2H, for example for semiconductor device **10**. FIGS. 7A to 7I, however, show valve **38** positioned at base **112A** of cavity substrate **11**. The following description will focus on differences between both methods.

[0054] FIG. 7A shows a cross-sectional view of semiconductor device **30** at an early stage of manufacture. In the example shown in FIG. 7A, cavity substrate **11** can be provided. Cavity substrate **11** can comprise base **112A** and sidewall **112B**. Base **112A** can have a substantially planar top side and a substantially planar bottom side opposite to the top side. Valve **38** can be provided to vertically pass through the top and bottom of base **112A**. In some examples, valve **38** can be provided through a chemical etching process, a laser beam process, or a mechanical drilling process.

[0055] In some examples, valve **38** can comprise a first, upper through-hole **38A** and a second, lower through-hole **38B** connected to each other. Upper through-hole **38A** connected to the top side of base **112A** can have a constant width, and lower through-hole **38B** connected to the bottom side of base **112A** can have a gradually increasing width toward the bottom side of base **112A**. A width of the second, lower through-hole **38B** at the bottom side of valve **38** can be greater than a width of the first, upper through-hole **38A**. Plug **19** can be in the second, lower through-hole **38B** to seal cavity **13**. In some examples, lower through-hole **38B** can be substantially semi-circular or bowl-shaped around the bottom side of base **112A**. In some examples, lower through-hole **38B** of valve **38** can comprise or be referred to as a dam or dam perimeter configured to restrain plug **19** from lateral displacement or expansion. Valve **38** can have a width in the range from about 50 μm to about 200 μm . The width of lower through-hole **38B** can be greater than the width of upper through-hole **38A**. In some examples, valve base **31** can be provided on a side of lower through-hole **38B**. In some examples valve base **31** can be metallic, comprising copper or tungsten formed on the side of lower through-hole **38B**, or a nickel-gold plating. In some examples, valve base **31** can be provided in a similar manner to conductive structure **111** described above. Valve base **31** can

have a thickness in the range from about 10 μm to about 50 μm .

[0056] FIG. 7B shows a cross-sectional view of semiconductor device **30** at a later stage of manufacture. In the example shown in FIG. 7B, electronic component **15** can be provided on cavity substrate **11**. In some examples, electronic component **15** can be attached onto base **112A** of cavity substrate **11** using an adhesive or a thermally conductive material.

[0057] FIG. 7C shows a cross-sectional view of semiconductor device **30** at a later stage of manufacture. In the example shown in FIG. 7C, interconnect **14** can be provided between electronic component **15** and cavity substrate **11**.

[0058] FIGS. 7D and 7E show a cross-sectional view of semiconductor device **30** at a later stage of manufacture. In the example shown in FIGS. 7D and 7E, lid **13** can be provided on cavity substrate **11**. A bottom side of lid **13** can be attached on sidewall **112B** of cavity substrate **11** using seal **16**. In some examples, the bottom side of lid **13** can be attached to seal base **1114** provided on sidewall **112B**.

[0059] FIG. 7F shows a cross-sectional view of semiconductor device **30** at a later stage of manufacture. In the example shown in FIG. 7F, cavity substrate **11** can be flipped such that lower through-hole **38B** provided on base **112A** faces upward.

[0060] FIG. 7G shows a cross-sectional view of semiconductor device **30** at a later stage of manufacture. In the example shown in FIG. 7G, air in cavity **113** can be discharged from cavity **113** through valve **38**, or a gas such as an inert gas or air can be introduced into cavity **113** through valve **38** to a target pressure.

[0061] FIG. 7H shows a cross-sectional view of semiconductor device **30** at a later stage of manufacture. In the example shown in FIG. 7H, plug **19** can be provided at valve **38** provided on base **112A**. In some examples, plug **19** can be positioned on bowl-shaped lower through-hole **38B** or valve base **31**. Accordingly, valve **38** can be occluded by plug **19**.

[0062] FIG. 7I shows a cross-sectional view of semiconductor device **30** at a later stage of manufacture. In the example shown in FIG. 7I, valve **38** can be occluded hermetically by melting plug **19**, or by performing a forced insertion or bolting of plug **19**, at lower through-hole **38B**.

[0063] FIG. 8 shows a cross-sectional view of an example semiconductor device **40**. Example semiconductor device **40** shown in FIG. 8 can be similar to example semiconductor device **10** shown in FIG. 1, and valve **48**, including valve base **41**, is provided between cavity substrate **11** and lid **13**. In the example shown in FIG. 8, semiconductor device **40** can be configured such that valve **48** is positioned between sidewall **112B** of cavity substrate **11** and lid **13**. Semiconductor device **40** can comprise plug **19** occluding valve **48**.

[0064] FIGS. 9A to 9H show cross-sectional views of an example method for manufacturing an example semiconductor device **40**. The manufacturing method of example semiconductor device **40** shown in FIGS. 9A to 9H can be similar to corresponding operations or figures described in FIGS. 2A to 2H, for example for semiconductor device **10**. FIGS. 9A to 9H, however, show that valve **48** is positioned between cavity substrate **11** and lid **13**. The following description will focus on differences between both methods.

[0065] FIG. 9A shows a cross-sectional view of semiconductor device **40** at an early stage of manufacture. In the example shown in FIG. 9A, cavity substrate **11** can be provided. Cavity substrate **11** can comprise base **112A** and sidewall **112B**, and valve **48** can be provided at a top of sidewall **112B**. Valve **48** can comprise or have groove **48A** recessed on sidewall **112B**. In some examples, groove **48A** can have a bowl-shaped cross section. Groove **48A** can be provided by performing a chemical etching process, a laser beam process, or a mechanical drilling process on the region of sidewall **112B**.

[0066] In some examples, valve **48** can further comprise valve base **41** provided on a side of groove **48A**. Valve base **41** can also have a bowl-shaped cross section, like the side of groove **48A**. In some examples, valve **48** can be connected to or can be part of seal base **1114**, can be made of a material similar to that of seal base **1114**, or can have a thickness similar to that of seal base **1114**.

In some examples, groove **48A** can have a depth in the range from about 50 μm to about 200 μm . In some examples, valve base **41** can comprise copper or tungsten formed on the side of groove **48A**, or a nickel-gold plating. Valve base **41** can have a thickness in the range from about 10 μm to about 50 μm .

[0067] FIG. **9B** shows a cross-sectional view of semiconductor device **40** at a later stage of manufacture. In the example shown in FIG. **9B**, electronic component **15** can be provided on cavity substrate **11**. In some examples, electronic component **15** can be attached onto base **112A** of cavity substrate **11** using an adhesive or a thermally conductive material.

[0068] FIG. **9C** shows a cross-sectional view of semiconductor device **40** at a later stage of manufacture. In the example shown in FIG. **9C**, interconnect **14** can be provided between electronic component **15** and cavity substrate **11**.

[0069] FIGS. **9D** and **9E** show a cross-sectional view of semiconductor device **40** at a later stage of manufacture. In the example shown in FIGS. **9D** and **9E**, lid **13** can be provided on cavity substrate **11**. A bottom side of lid **13** can be attached onto sidewall **112B** or seal base **1114** using seal **16**. Seal **16** can comprise a gap between sidewall **112B** and lid **13**, and the gap can comprise or be defined valve **48**. Valve **48** can have a width, including a width of the gap, in the range from about 50 μm to about 200 μm .

[0070] FIG. **9F** shows a cross-sectional view of semiconductor device **40** at a later stage of manufacture. In the example shown in FIG. **9F**, air in cavity **113** can be discharged from cavity **113** through valve **38**, or a gas such as an inert gas or air can be introduced into cavity **113** through valve **38** to a target pressure.

[0071] FIG. **9G** shows a cross-sectional view of semiconductor device **40** at a later stage of manufacture. In the example shown in FIG. **9G**, plug **19** can be provided at valve **48** positioned between cavity substrate **11** and lid **13**. Plug **19** can be mounted on valve **48** positioned on sidewall **112B** of cavity substrate **11**. In some examples, plug **19** can be positioned at an entrance of valve **48** or on groove **48A**. Accordingly, valve **48** can be occluded by plug **19**.

[0072] FIG. **9H** shows a cross-sectional view of semiconductor device **40** at a later stage of manufacture. In the example shown in FIG. **9H**, valve **48** can be occluded hermetically by melting plug **19** or by performing a forced insertion or bolting of plug **19** into valve **48** or groove **48A**. In some examples, groove **48A** of valve **48** can comprise or be referred to as a dam or dam perimeter configured to restrain plug **19** from lateral displacement or expansion. In some examples, plug **19** can be made of a material that is the same as or similar to that of seal **16**.

[0073] FIG. **10** shows a cross-sectional view of an example semiconductor device **50**. Example semiconductor device **50** shown in FIG. **10** can be similar to example semiconductor device **10** shown in FIG. **1**, and valve **58** is provided at lid **13**, rather than at cavity substrate **11**. In the example shown in FIG. **10**, semiconductor device **50** can comprise lid **13** having valve **58**. Valve **58** of lid **13** can further comprise valve base **51**. Semiconductor device **50** can comprise plug **19** occluding valve **58** of lid **13**.

[0074] FIGS. **11A** to **11F** show cross-sectional views of an example method for manufacturing an example semiconductor device **50**. The manufacturing method of example semiconductor device **50** shown in FIGS. **11A** to **11F** can be similar to corresponding operations or figures described in FIGS. **2A** to **2H**, for example for semiconductor device **10**. Valve **58**, however, is provided on lid **13**, rather than on cavity substrate **11**. The following description will focus on differences between both methods.

[0075] FIG. **11A** shows a cross-sectional view of semiconductor device **50** at an early stage of manufacture. In the example shown in FIG. **11A**, lid **13** having valve **58** can be provided. Lid **13** can have a substantially planar top side and a substantially planar bottom side. Valve **58** comprising or having through-hole **58A** passing through top and bottom sides of lid **13** can be provided. Through-hole **58A** can be in lid **13** between lid **13** and sidewall **112B** of cavity substrate **11**. In some examples, valve **58** can be substantially circular or bowl-shaped. In some examples, through-

hole **58A** of valve **58** can be provided while passing through base **112A** through a chemical etching process, a laser beam process, or a mechanical drilling process. In some examples, valve base **51** can further be provided on inner wall of through-hole **58A**. In some examples, valve base **51** can be made of a material similar to that of seal base **1114**. In some examples, valve base **51** can have a thickness in the range from about 10 μm to about 50 μm . Valve **58** provided on lid **13** can correspond to or be aligned with a region of seal base **1114** provided on cavity substrate **11**.

[0076] FIGS. **11B** and **11C** show a cross-sectional view of semiconductor device **50** at a later stage of manufacture. In the example shown in FIGS. **11B** and **11C**, lid **13** can be provided on cavity substrate **11**. A bottom side of lid **13** can be attached to the top of sidewall **112B** or seal base **1114** of cavity substrate **11** using seal **16**. Seal **16** can be provided with a gap around valve **58**, such that valve **58** is not occluded by seal **16**.

[0077] FIG. **11D** shows a cross-sectional view of semiconductor device **50** at a later stage of manufacture. In the example shown in FIG. **11D**, the air in cavity **113** can be discharged from cavity **113** through valve **58**, or a gas such as an inert gas or air can be introduced into cavity **113** through valve **58** to a target pressure.

[0078] FIG. **11E** shows a cross-sectional view of semiconductor device **50** at a later stage of manufacture. In the example shown in FIG. **11E**, plug **19** can be provided at an entrance of valve **58**, through lid **13**, to occlude valve **58**.

[0079] FIG. **11F** shows a cross-sectional view of semiconductor device **50** at a later stage of manufacture. In the example shown in FIG. **11F**, valve **58** provided in lid **13** and the gap created between lid **13** and cavity substrate **11** can be hermetically occluded by plug **19**. In some examples, valve **58** and the gap can be occluded by melting plug **19**, or by performing a forced insertion or bolting of plug **19** at valve **58**.

[0080] FIG. **11F** shows a cross-sectional view of semiconductor device **50** at a later stage of manufacture. In the example shown in FIG. **11F**, valve **58** can be occluded hermetically by melting plug **19** or by performing a forced insertion or bolting of plug **19** into valve **58** or through-hole **58A**. In some examples, plug **19** can be made of a material the same as or similar to that of seal **16**.

[0081] The present disclosure includes reference to certain examples. It will be understood, however, by those skilled in the art that various changes may be made, and equivalents may be substituted without departing from the scope of the disclosure. In addition, modifications may be made to the disclosed examples without departing from the scope of the present disclosure. Therefore, it is intended that the present disclosure is not limited to the examples disclosed, but that the disclosure will include all examples falling within the scope of the appended claims.

Claims

1. A semiconductor device, comprising: a cavity substrate comprising a base and a sidewall to define a cavity; an electronic component on a top side of the base in the cavity; a lid over the cavity and over the sidewall; and a valve to provide access to the cavity, wherein the valve has a plug to provide a seal between a cavity environment and an exterior environment outside the cavity.
